

ABSTRACT OF THE DISCLOSURE

A method for forming a gate of a high integration semiconductor device in which, when forming a gate electrode on a semiconductor substrate by depositing a 5 nitride layer and an anti-reflection layer after depositing a conductive layer constructed by a gate oxide layer, a polysilicon layer, a tungsten nitride layer and a tungsten layer, an etch prevention layer is formed between the nitride layer and the anti-reflection layer 10 in order to prevent the nitride layer from over-etching, thereby preventing the leakage current, caused by the bridge formed between the gate and the bit line, from generating.